

ESD Protection Diodes

Ultra Low Capacitance ESD Protection Diode for High Speed Data Line

ESD8101, ESD8111

The ESD81x1 Series ESD protection diodes are designed to protect high speed data lines from ESD. Ultra-low capacitance and low ESD clamping voltage make this device an ideal solution for protecting voltage sensitive high speed data lines.

Features

- Low Capacitance (0.20 pF Typ, I/O to GND)
- Protection for the Following IEC Standards:
IEC 61000-4-2 (Level 4)
- Low ESD Clamping Voltage
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Typical Applications

- USB 3.0/3.1
- MHL 2.0
- eSATA

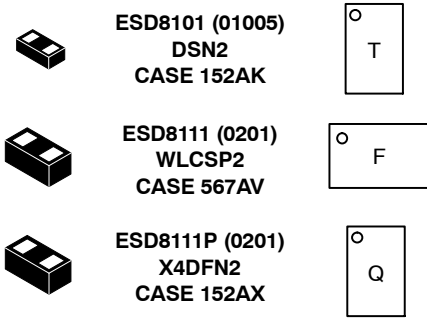
MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Operating Junction Temperature Range	T _J	-55 to +150	°C
Storage Temperature Range	T _{stg}	-55 to +150	°C
Lead Solder Temperature – Maximum (10 Seconds)	T _L	260	°C
ESD8101: IEC 61000-4-2 Contact IEC 61000-4-2 Air	ESD	±23	kV
ESD8111: IEC 61000-4-2 Contact IEC 61000-4-2 Air		±30	kV

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

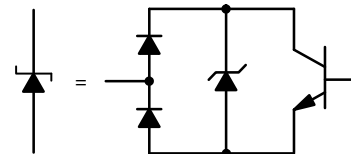
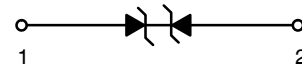
See Application Note AND8308/D for further description of survivability specs.

MARKING DIAGRAMS



T, F, Q = Device Code

PIN CONFIGURATION AND SCHEMATIC



ORDERING INFORMATION

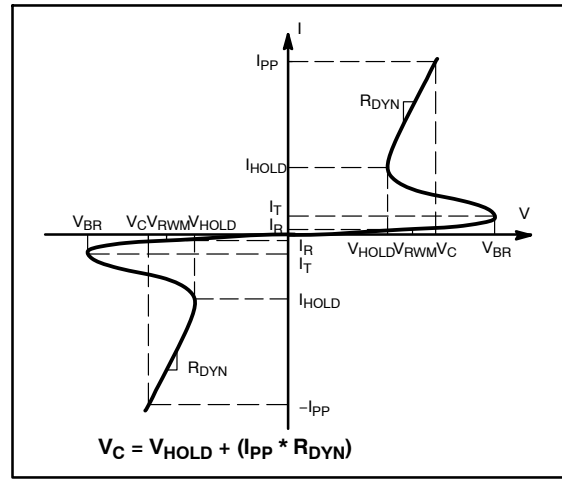
See detailed ordering and shipping information on page 2 of this data sheet.

ESD8101, ESD8111

ELECTRICAL CHARACTERISTICS

(T_A = 25°C unless otherwise noted)

Symbol	Parameter
V _{RWM}	Working Peak Voltage
I _R	Maximum Reverse Leakage Current @ V _{RWM}
V _{BR}	Breakdown Voltage @ I _T
I _T	Test Current
V _{HOLD}	Holding Reverse Voltage
I _{HOLD}	Holding Reverse Current
R _{DYN}	Dynamic Resistance
I _{PP}	Maximum Peak Pulse Current
V _C	Clamping Voltage @ I _{PP} V _C = V _{HOLD} + (I _{PP} * R _{DYN})



ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse Working Voltage	V _{RWM}	I/O Pin to GND			3.3	V
Breakdown Voltage	V _{BR}	I _T = 1 mA, I/O Pin to GND	5.5	7.9	8.6	V
Reverse Leakage Current	I _R	V _{RWM} = 3.3 V, I/O Pin to GND			1.0	μA
Reverse Holding Voltage	V _{HOLD}	I/O Pin to GND		2.1		V
Holding Reverse Current	I _{HOLD}	I/O Pin to GND		17		mA
ESD8111 Clamping Voltage	V _C	I _{PP} = 7.1 A, (8/20 μs pulse)			8.0	V
ESD8101, ESD8111 Clamping Voltage TLP (Note 1)	V _C	I _{PP} = 8 A } IEC 61000-4-2 Level 2 equivalent (±4 kV Contact, ±4 kV Air)		6.5		V
		I _{PP} = 16 A } IEC 61000-4-2 Level 4 equivalent (±8 kV Contact, ±15 kV Air)		10		V
Dynamic Resistance	R _{DYN}	I/O Pin to GND		0.46		Ω
Junction Capacitance	C _J	V _R = 0 V, f = 1 MHz		0.2	0.4	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. ANSI/ESD STM5.5.1 – Electrostatic Discharge Sensitivity Testing using Transmission Line Pulse (TLP) Model.

TLP conditions: Z₀ = 50 Ω, t_p = 100 ns, t_r = 4 ns, averaging window; t₁ = 30 ns to t₂ = 60 ns.

ORDERING INFORMATION

Device	Package	Shipping†
ESD8101FCT5G	DSN2 (Pb-Free)	10,000 / Tape & Reel
ESD8111FCT5G	WLCSP2 (Pb-Free)	10,000 / Tape & Reel
ESD8111PFCT5G	WLCSP2 Side wall Isolated 0201 (Pb-Free)	10,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ESD8101, ESD8111

TYPICAL CHARACTERISTICS

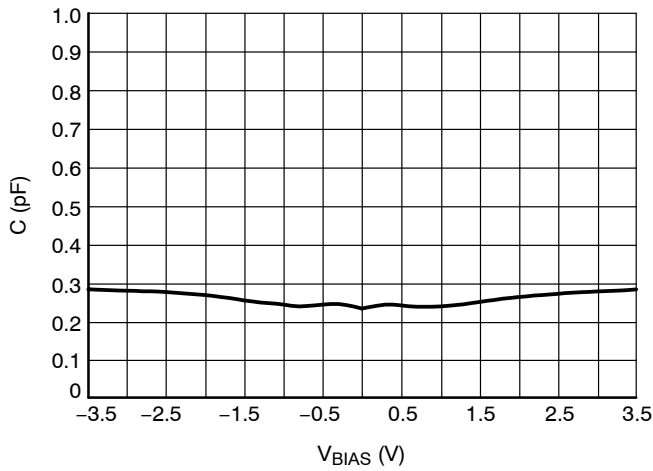


Figure 1. ESD8101 CV Characteristics

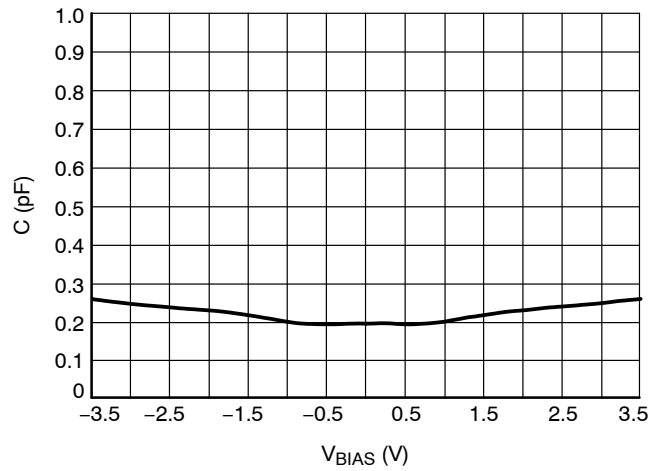


Figure 2. ESD8111 CV Characteristics

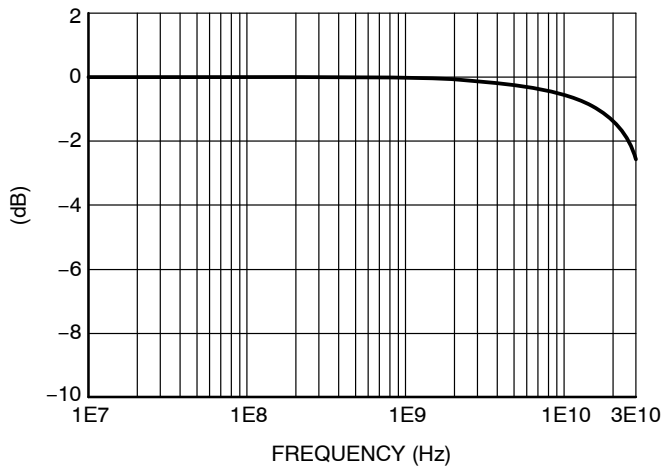


Figure 3. ESD8101 S21 Insertion Loss

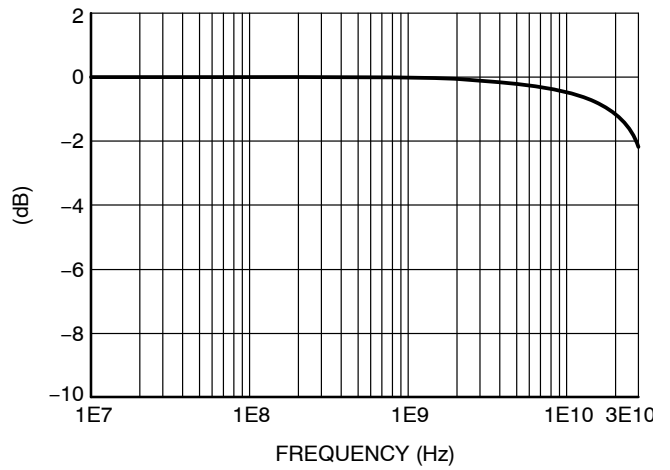


Figure 4. ESD8111 S21 Insertion Loss

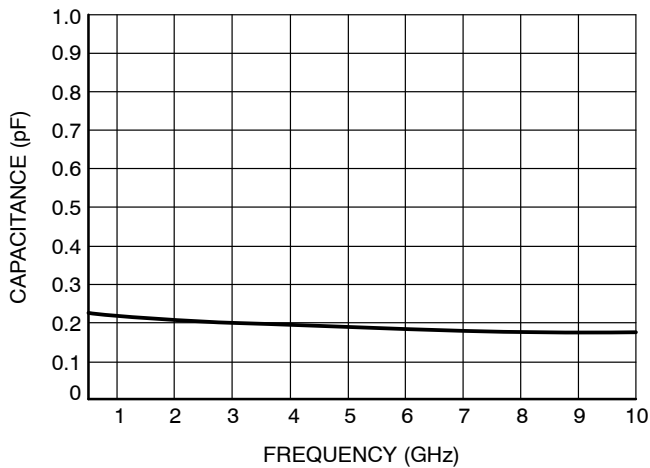


Figure 5. ESD8101 Capacitance over Frequency

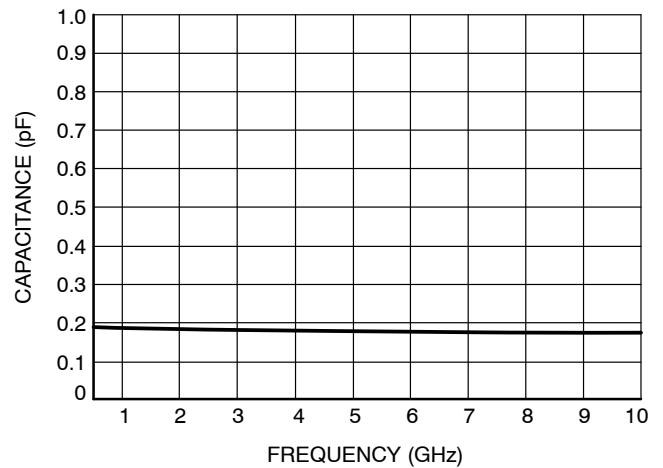


Figure 6. ESD8111 Capacitance over Frequency

ESD8101, ESD8111

TYPICAL CHARACTERISTICS

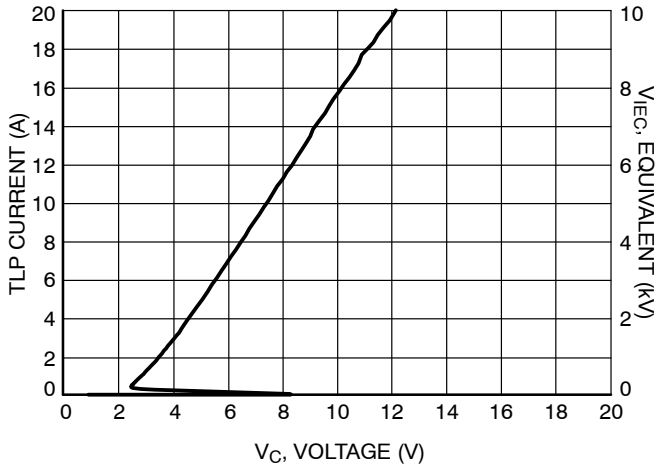


Figure 7. ESD8101 Positive TLP I-V Curve

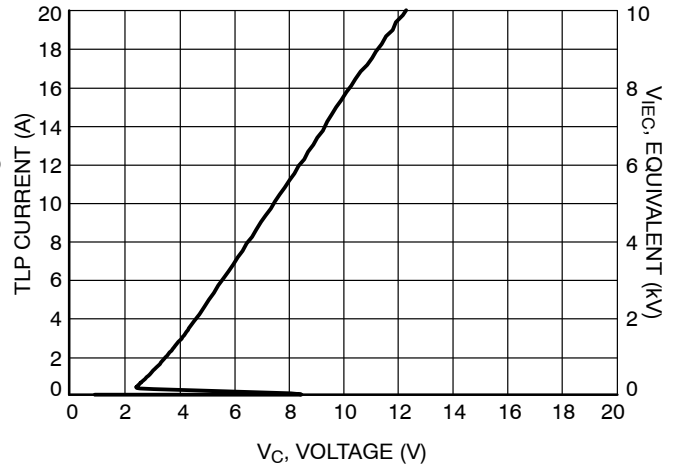


Figure 8. ESD8111 Positive TLP I-V Curve

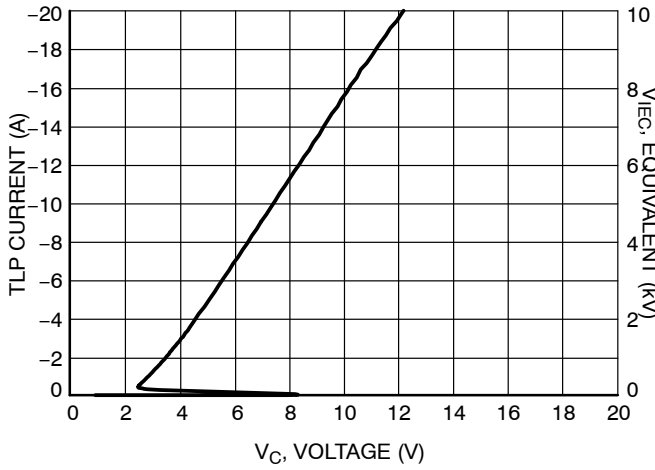


Figure 9. ESD8101 Negative TLP I-V Curve

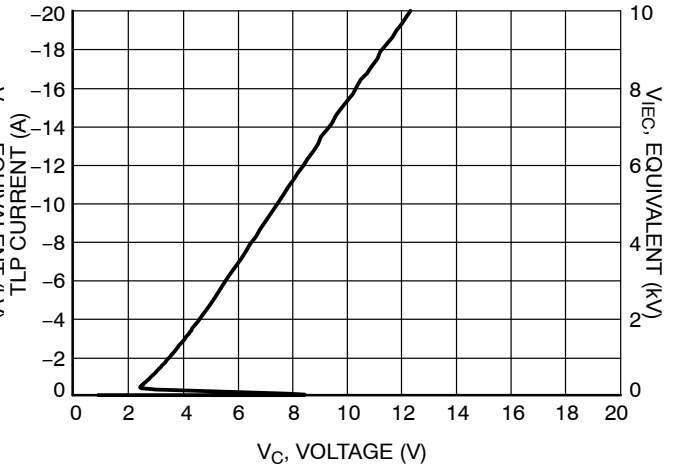


Figure 10. ESD8111 Negative TLP I-V Curve

ESD8101, ESD8111

IEC 61000-4-2 Spec.

Level	Test Voltage (kV)	First Peak Current (A)	Current at 30 ns (A)	Current at 60 ns (A)
1	2	7.5	4	2
2	4	15	8	4
3	6	22.5	12	6
4	8	30	16	8



Figure 11. IEC61000-4-2 Spec

Transmission Line Pulse (TLP) Measurement

Transmission Line Pulse (TLP) provides current versus voltage (I-V) curves in which each data point is obtained from a 100 ns long rectangular pulse from a charged transmission line. A simplified schematic of a typical TLP system is shown in Figure 12. TLP I-V curves of ESD protection devices accurately demonstrate the product's ESD capability because the 10s of amps current levels and under 100 ns time scale match those of an ESD event. This is illustrated in Figure 13 where an 8 kV IEC 61000-4-2 current waveform is compared with TLP current pulses at 8 A and 16 A. A TLP I-V curve shows the voltage at which the device turns on as well as how well the device clamps voltage over a range of current levels.



Figure 12. Simplified Schematic of a Typical TLP System

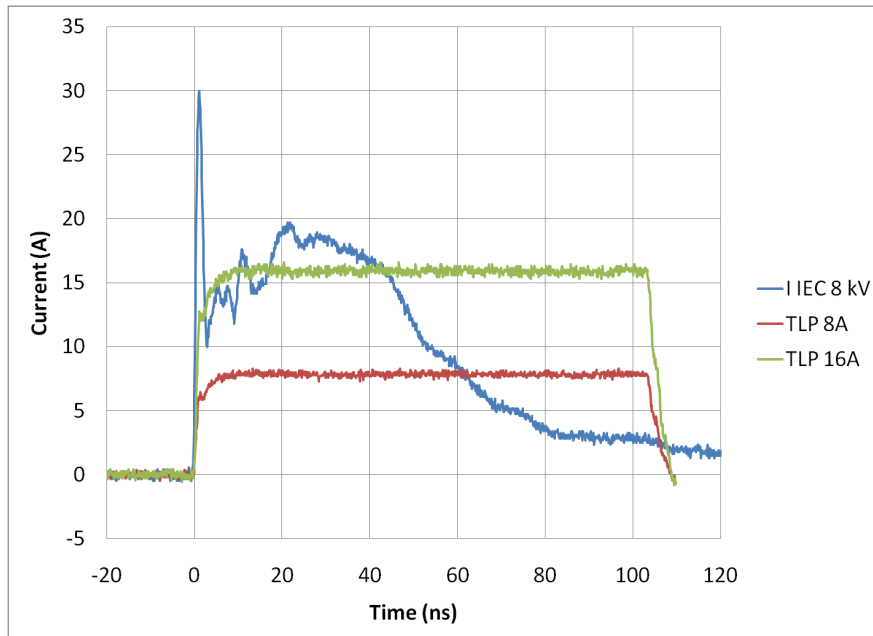


Figure 13. Comparison Between 8 kV IEC 61000-4-2 and 8 A and 16 A TLP Waveforms

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

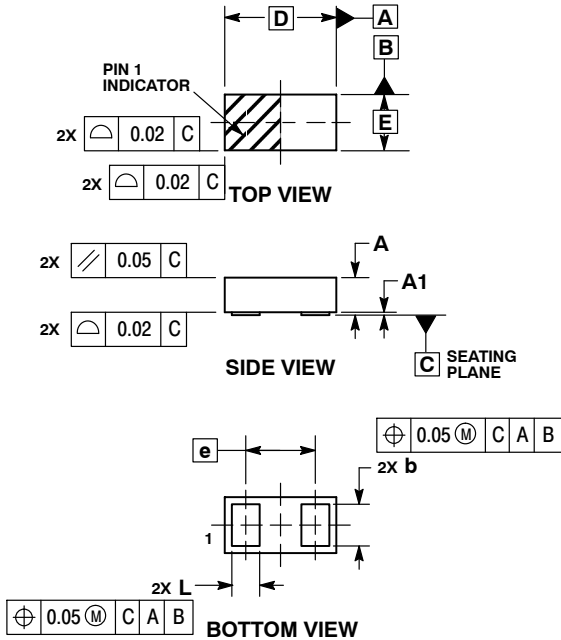
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SCALE 16:1

DSN2, 0.435x0.23, 0.27P, (01005)
CASE 152AK
ISSUE A

DATE 17 FEB 2015



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.

MILLIMETERS		
DIM	MIN	MAX
A	0.165	0.195
A1	---	0.030
b	0.177	0.193
D	0.435 BSC	
E	0.230 BSC	
e	0.270 BSC	
L	0.112	0.128

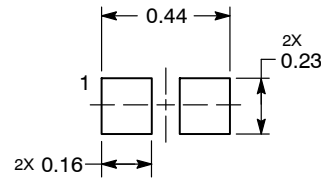
GENERIC MARKING DIAGRAM*



X = Specific Device Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G", may or not be present.

RECOMMENDED SOLDER FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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DESCRIPTION:	DSN2, 0.435X0.23, 0.27P (01005)	PAGE 1 OF 1

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MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

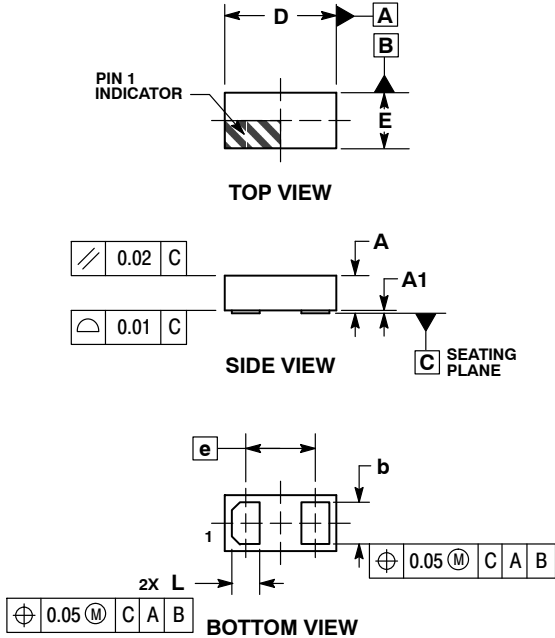
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SCALE 8:1

X4DFN2, 0.60x0.30, 0.36P
CASE 152AX
ISSUE G

DATE 12 APR 2019

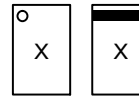


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.

MILLIMETERS			
DIM	MIN	NOM	MAX
A	0.175	0.200	0.225
A1	0.018 REF		
b	0.205	0.215	0.225
D	0.575	0.600	0.625
E	0.275	0.300	0.325
e	.36 BSC		
L	0.145	0.155	0.165

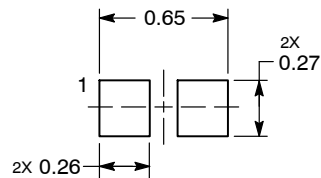
GENERIC MARKING DIAGRAM*



X = Specific Device Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G", may or not be present. Some products may not follow the Generic Marking.

RECOMMENDED SOLDER FOOTPRINT*



DIMENSIONS: MILLIMETERS

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DESCRIPTION:	X4DFN2, 0.60x0.30, 0.36P	PAGE 1 OF 1

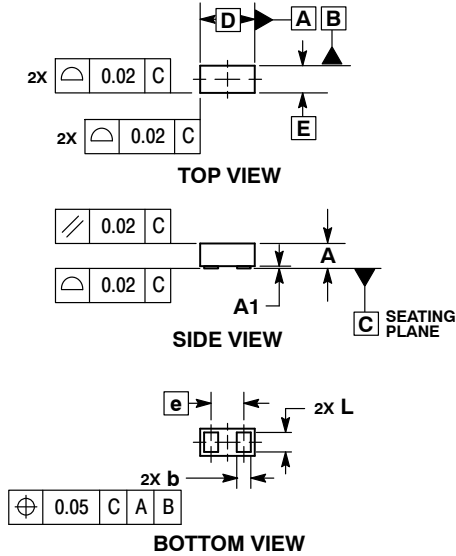
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SCALE 12:1

WLCSP2, 0.6x0.3
CASE 567AV
ISSUE C

DATE 22 SEP 2017



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.

MILLIMETERS			
DIM	MIN	NOM	MAX
A	0.250	0.275	0.300
A1	0.000	0.025	0.050
b	0.140	0.155	0.170
D	0.570	0.600	0.630
E	0.270	0.300	0.330
e	0.36 BSC		
L	0.190	0.215	0.240

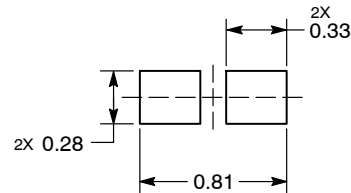
GENERIC MARKING DIAGRAM*



X = Specific Device Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

RECOMMENDED SOLDER FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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DESCRIPTION:	WLCSP2, 0.6X0.3	PAGE 1 OF 1

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